



Docket No.: R2184.0052/P052-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Naoto Jikutani et al.

Application No.: 09/391,472

Group Art Unit: 1765

Filed: September 8, 1999

Examiner: R. Kunemund

For: LASER DIODE HAVING AN ACTIVE
LAYER CONTAINING N AND OPERABLE
IN A 0.6 μ m WAVELENGTH BAND

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached Form PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

The listed documents are not being supplied because they were cited in either one of, or both of, prior Application No. 09/289,955, filed April 13, 1999, now U.S. Patent No. 6,563,851, relied upon in this application for an earlier filing date under 35 U.S.C. § 120, or related Application No. 10/428,074, filed May 2, 2003.

Application No.: 09/391,472

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Dated: September 4, 2002

Respectfully submitted,

By 

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PTO/SB/08a/b (06-03)

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U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	09/391,472
				Filing Date	September 8, 1999
				First Named Inventor	Naoto Jikutani
				Art Unit	1765
				Prior Examiner Name	R. Kunemund
Sheet	1	of	1	Attorney Docket Number	R2184.0052/P052-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	AA	4,745,612 A	05/1988	Hayakawa et al.	
	AB	5,383,211 A	01/1995	Van de Walle et al.	
	AC	5,585,649 A	12/1996	Ishikawa et al.	
	AD	6,150,677 A	11/2000	Tanaka et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	AE	Ougazzaden et al., "Metal Organic Vapor Phase Epitaxy Growth of GAsN on GaAs Using Dimethylhydrazine and Tertiarybutylarsine," Applied Physics Letters, Vol. 70, No. 21, May 26, 1997, pp. 2861-2863	

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